The University of Tokushima (2011)) Graduate School of Advanced Technology and Science) Electrical and Electronic Engineering (Master) [=>Japanese]

Advanced Theory of Optelectronics

Masao Nagase · Professor / Material and Device Science, Electrical and Electronic Engineering, Systems Innovation Engineering

2 units (selection)

- Target > The purpose of this class is to understand principles of new devices based on semiconductor physics
 Outline > Basis and applications of semiconductor devices fabricated using
- **Outline**) Basis and applications of semiconductor devices fabricated using nanotechnology are introduced.

Style> Lecture

Keyword > nanotechnology, semiconductor physics, electron device

$\textbf{Goal}\rangle$

- 1. understanding of semiconductor physics
- 2. understanding of nano-fabrication
- 3. understanding of nano-metrology
- 4. understanding of principles of nano-devices

Schedule

- **1.** Introduction(1 week)
- 2. Semiconductor physics (3 weeks)
- **3.** Nano-fabrication (3 weeks)
- 4. Nano-metrology (3 weeks)
- 5. Nano-devices (4 weeks)
- 6. Future prospects of nano-electronics (2 weeks)

Evaluation Criteria Examinations and portfolios

Textbook> Printed materials

Contents http://cms.db.tokushima-u.ac.jp/cgi-bin/toURL?EID=216820

Student> Able to be taken by only specified class(es)

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Note A lecture name will be changed to "Advanced Theory of Nanoelectronics".